



Effect of Incoming Quality of Sulfuric Acid on Inline Defects

Dhiman Bhattacharyya*, Sushil Patil, Mark Conrad, Hayley Manning, Fauzia Khatkhatay, Alexander Mena and Norberto DeOliveira

March 28, 2017

Dhiman Bhattacharyya, Ph.D.
GLOBALFOUNDRIES
400 Stonebreak Rd. Ext., Malta, NY - 12020
Mobile: 518-415-2311
Email: dhiman.bhattacharyya@globalfoundries.com

SPCC 2017
Surface Preparation and Cleaning Conference

Outline

- ❑ Background
- ❑ Problem Statement
- ❑ Root cause investigation and results
- ❑ Summary



Outline

- ❑ **Background**
- ❑ **Problem Statement**
- ❑ **Root cause investigation and results**
- ❑ **Summary**

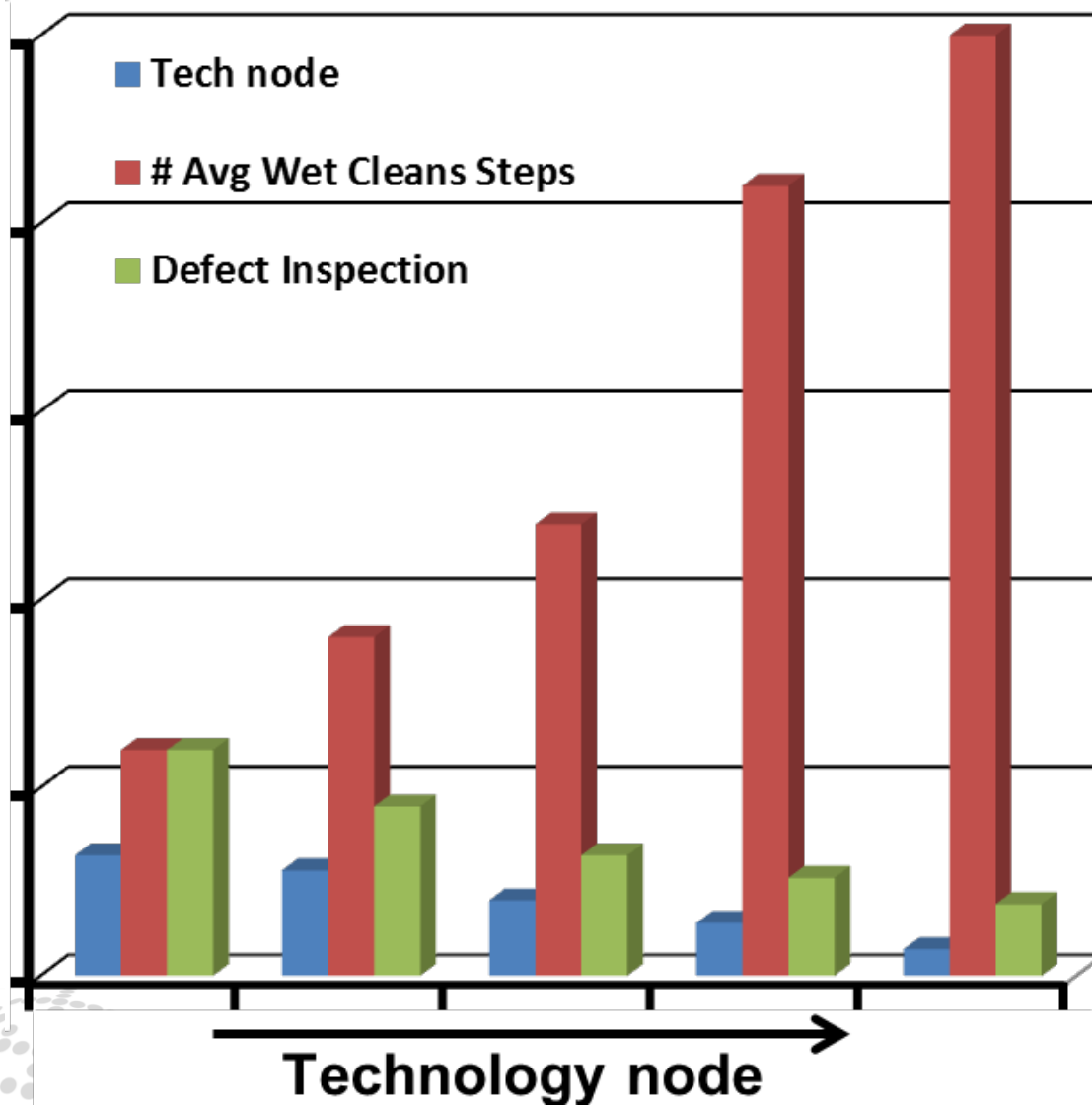


Background

- Hydrogen peroxide and sulfuric acid are the major consumables in Cleans.
- They are used in mixture in conventional cleans as Sulfuric and Peroxide Mixture (SPM or Piranha) which is then followed by Ammonia Peroxide Mixture (APM or SC1 or RCA1).
- Wet cleans using SPM is predominant in FEOL.
- High volume device manufacturers need to have multiple sources of materials for continuous supply chain.
- Any particle excursion in any chemical can potentially degrade the inline defects.



Background



- Technology is shrinking,
- Wet cleans contribution to keep the wafers clean is significantly increasing,
- Sensitivity of Dark Field detection is increasing.



Background

Detection Limitation:

- Difficult to detect any excursion in incoming particles if the particles are smaller than the detection limit.
- Current state of the art detection limit is 45nm by liquid particle counter.
- Inline defect detection can also miss the defects on the wafer in similar situations where defects are smaller than the detection limit.

Variability in sulfuric acid manufacturing:

- Sulfuric acid is usually produced using either glass or Teflon-lined steel absorption tower in high volume manufacturing environment.
- Glass lined column may introduce silica like particles.
- Teflon lined column may introduce carbon particles.

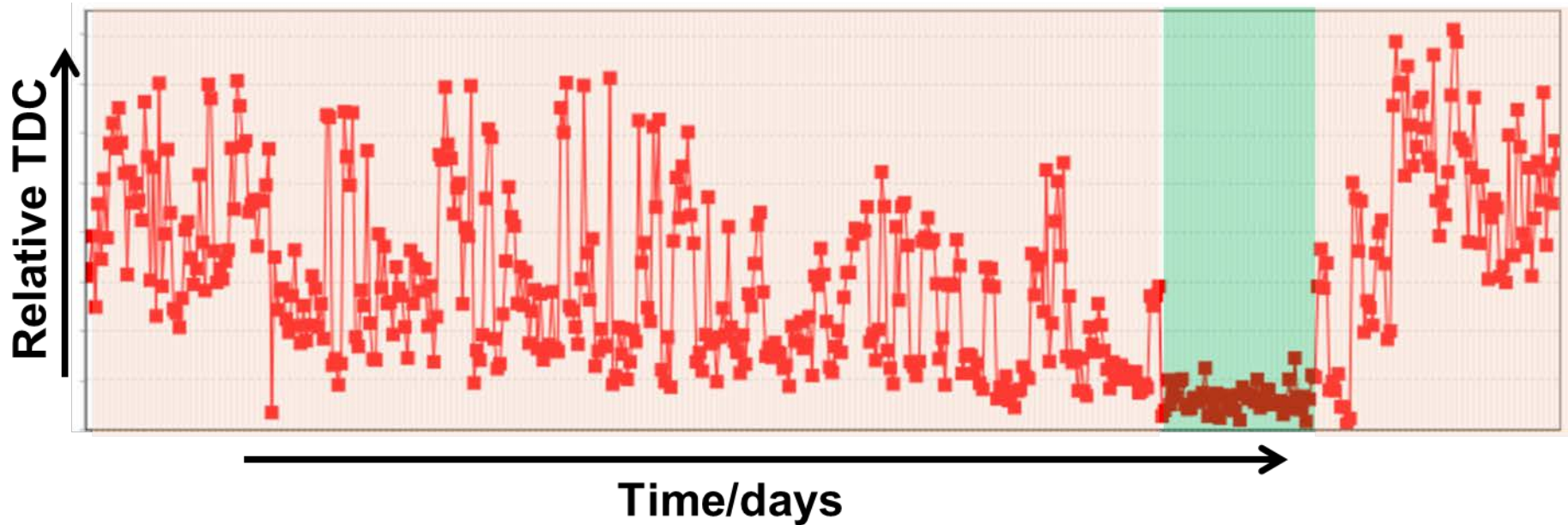


Outline

- Background
- **Problem Statement**
- Root cause investigation and results
- Summary



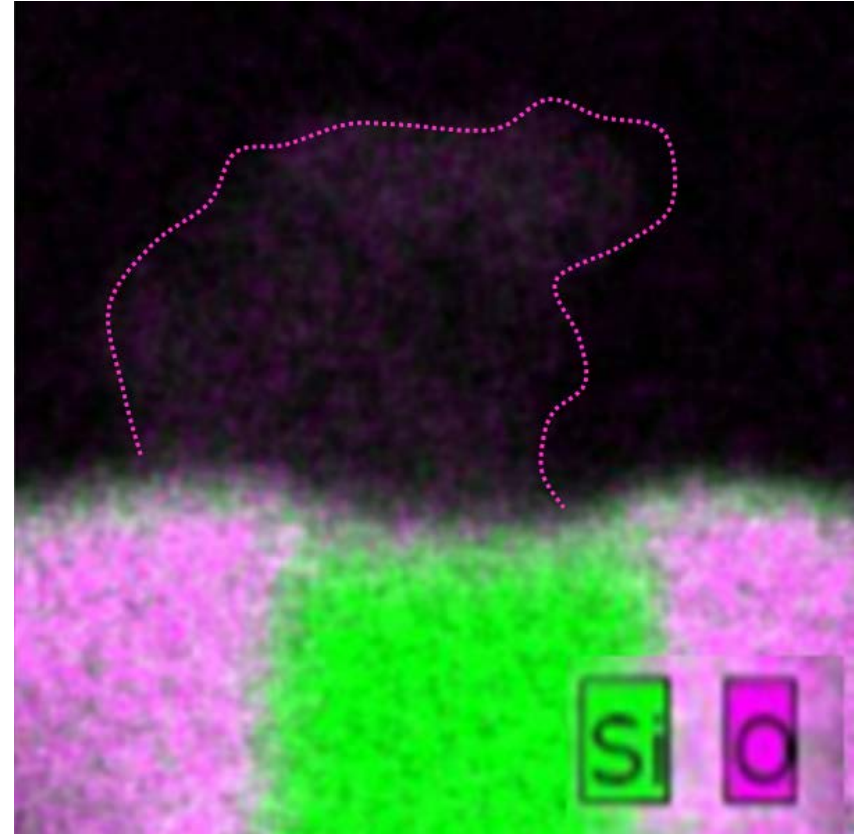
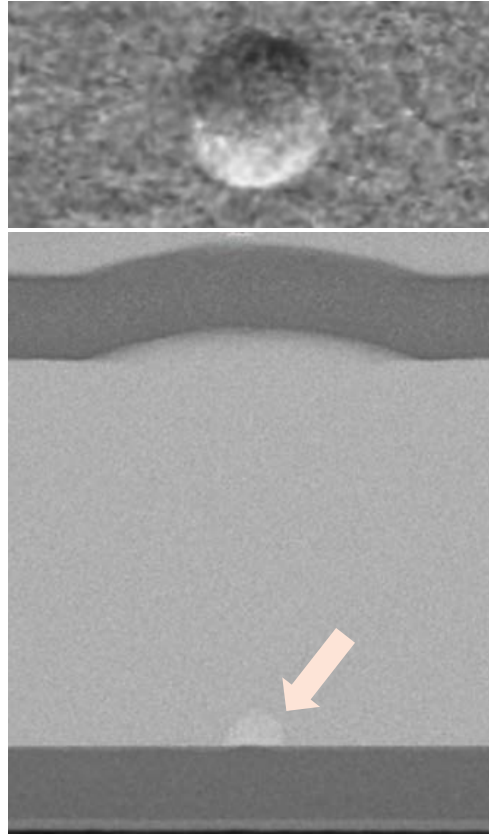
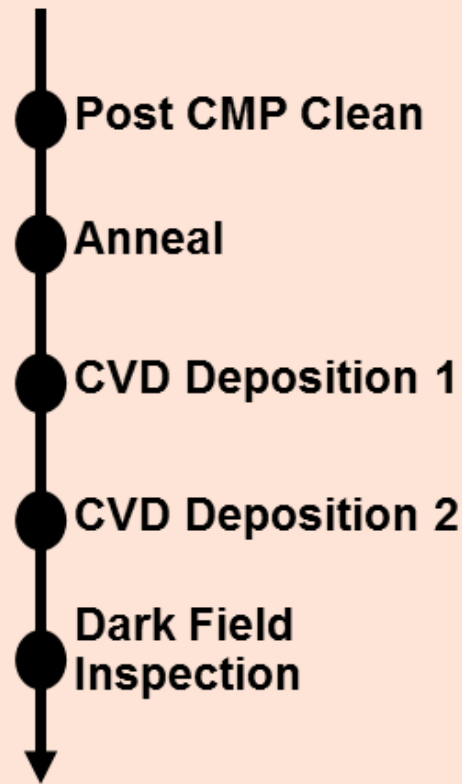
Problem Statement:



- The relative TDC (total defect counts) at a DF inspection step continuously improved over the time.
- Baseline defectivity significantly reduced.
- However, the TDCs jumped back to old baseline all of a sudden with no apparent correlation to any process or equipment or environmental changes.



Problem Statement:



- This DF inspection detects any excursion in Post CMP Clean as embedded defects.
- Even particles as small as ~10nm are visible as embedded after being decorated by 2 CVD films.
- DA clearly showed that the particles were composed of Si & O.

Outline

- Background
- Problem Statement
- **Root cause investigation and results**
- Summary



Root cause investigation and results

Approaches to identify the root cause of these defects;

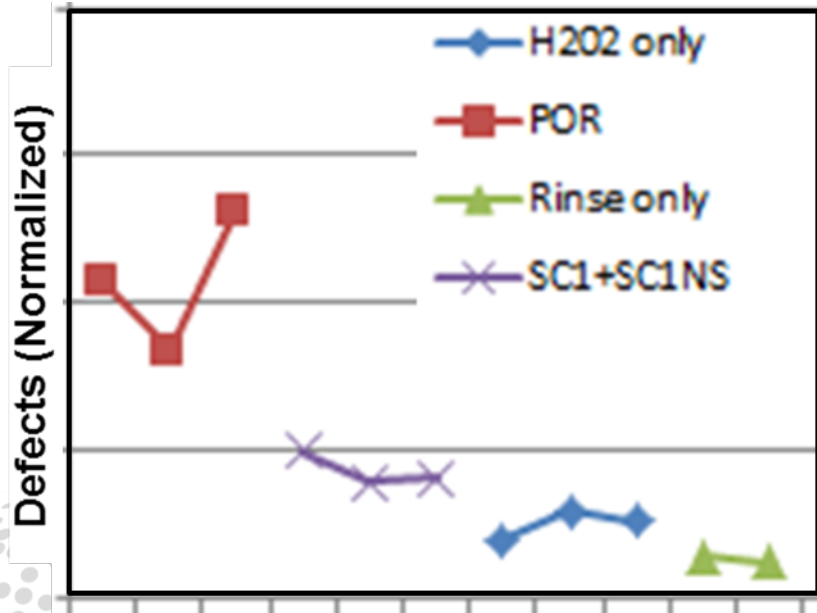
- (1) Failure analysis of the particles,
- (2) Comparison of defects from various components of the production recipe to conclude the defect source,
- (3) Comparison of defects from cleans process recipes with different SPM dispense times, and
- (4) Analysis of the defect trend versus the supply chain in real-time.



Root cause investigation and results

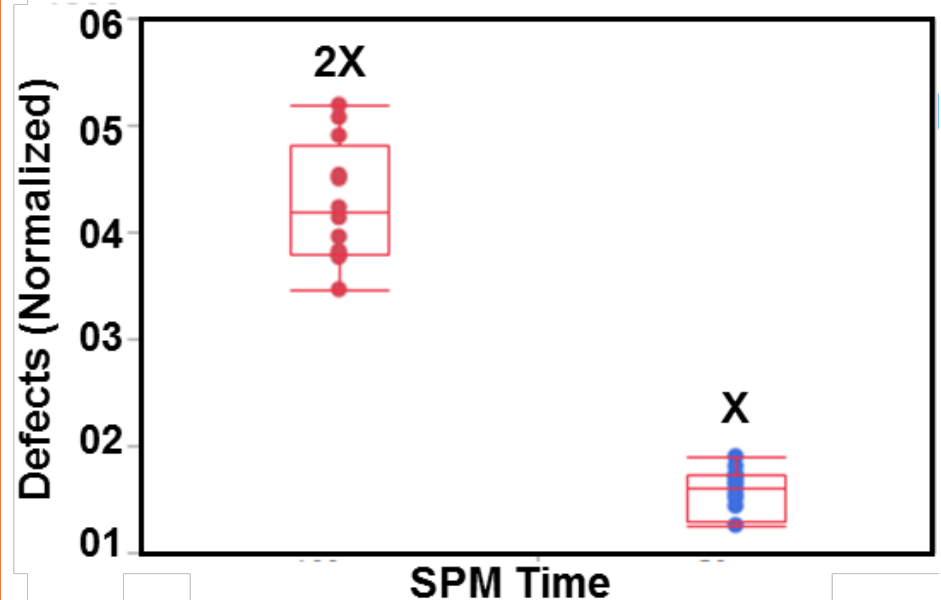
Comparison of defects from various components of the production recipe:

- The recipe was broken down into each chemistry.
- POR recipe, only which had SPM in it showed highest defect counts.

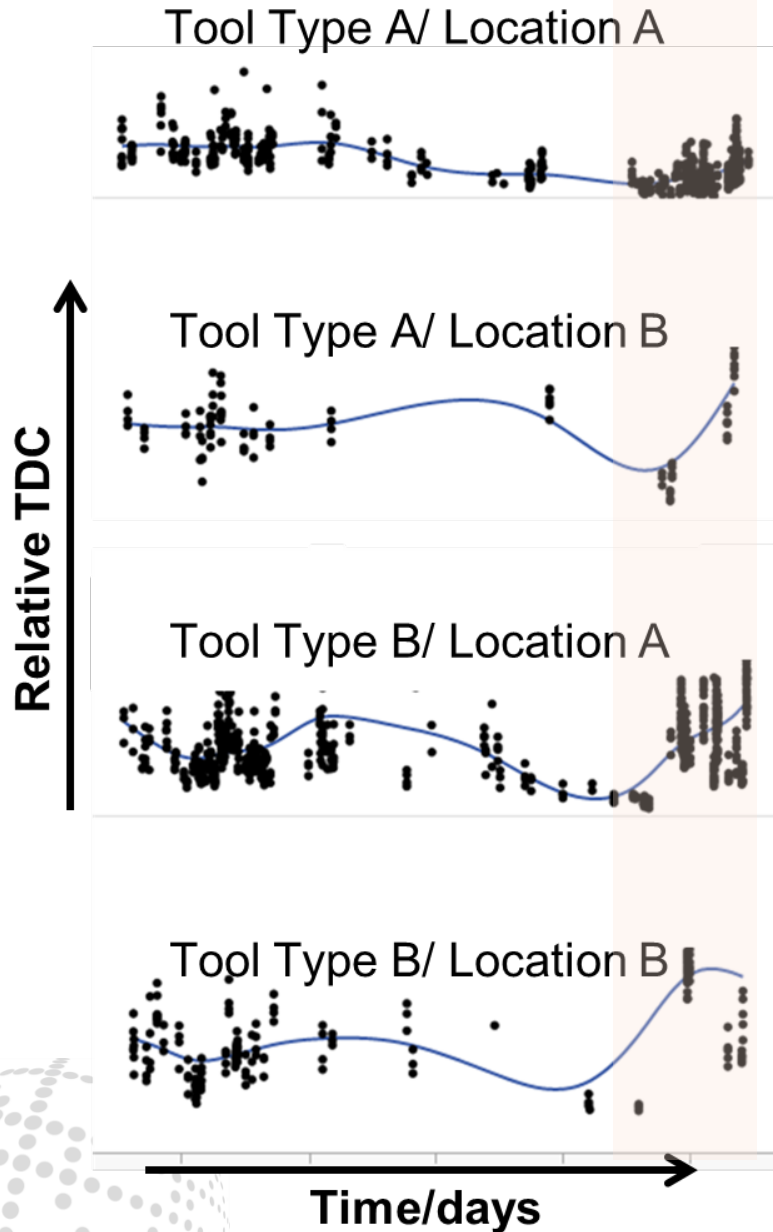


Comparison of defects from cleans process recipes with different SPM dispense times:

- An experiment with 50% reduced SPM dispense time at the same operation was performed.
- It helped in >75% reduction of the defects



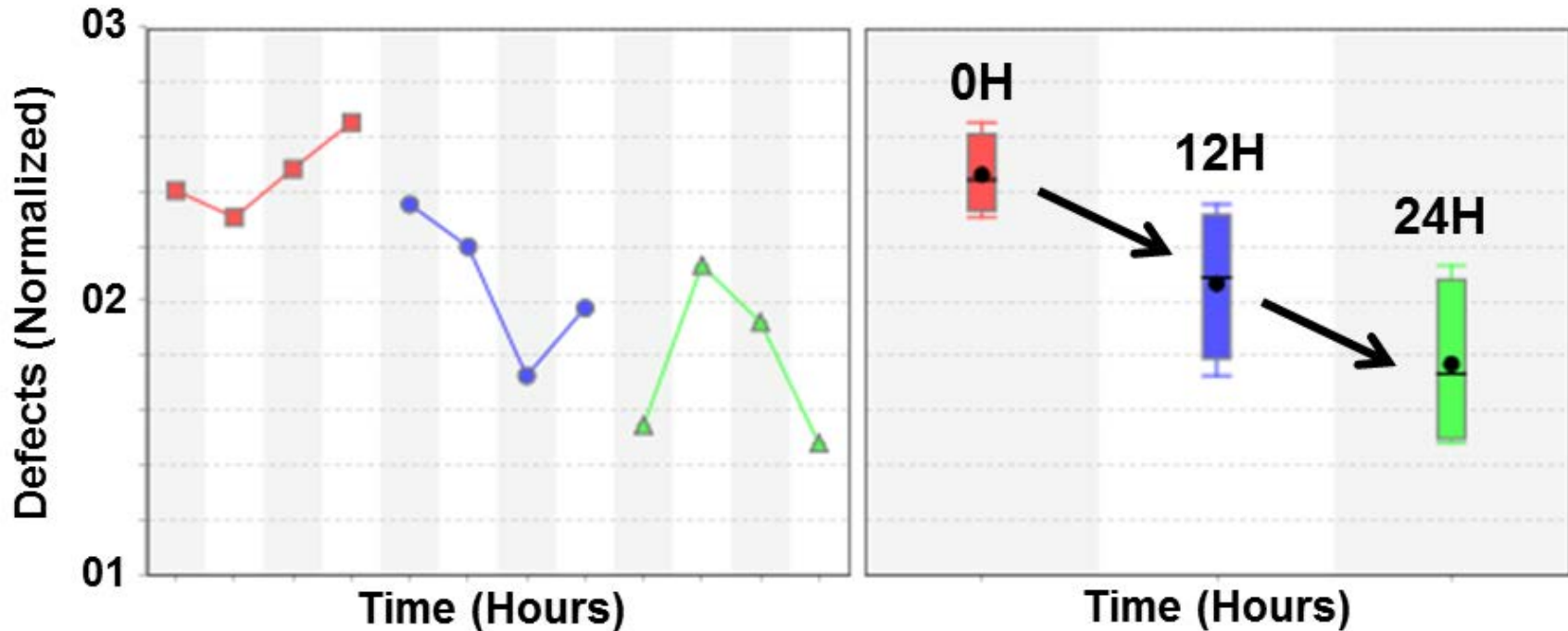
Root cause investigation and results



- Initial investigation was limited to very specific tools located to a specific location.
- The sensitivity of such tools in such location was in doubt.
- As time progressed, a clear uptrend in TDCs was noticed in all kinds of tools independent of where they were located.



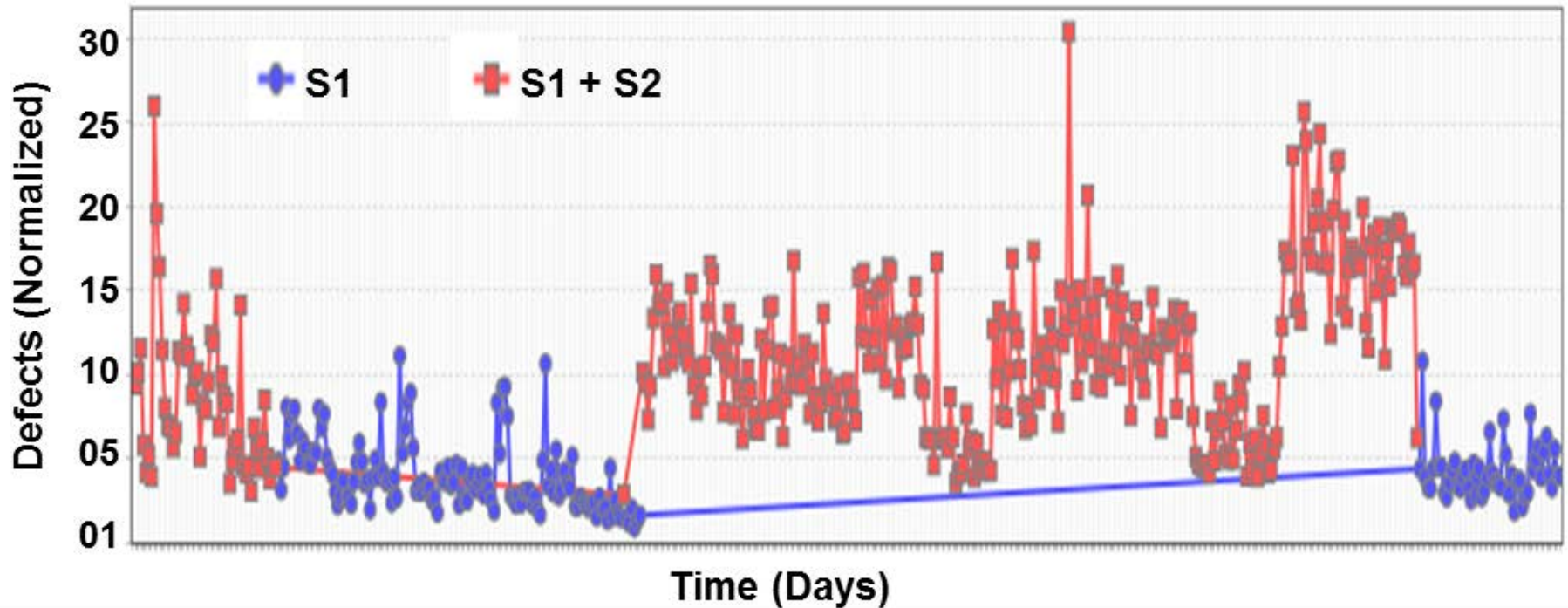
Root cause investigation and results



- A real-time experiment was carried out where the sulfuric acid manufactured in glass-lined steel absorption tower was stopped at the chemical feeder pump while the other source was continued to supply the operations.
- One experimental lot (12 wafers) was split in to three and each of the three sub-lots was processed at the post-CMP operation at a 12 hour interval.
- A very clear downtrend of defects in real-time was observed when the supply was flushing the silica contaminated material out.



Root cause investigation and results



- Sulfuric acid has been used in bulk from both the suppliers (S1 and S2).
- The defect baseline came down when supply from S2 was interrupted for few months.
- Baseline trended up again when supply from S2 was restored.
- Defect level trended down after supply from S2 was stopped.
- S2 was found to have glass lined column while S1 had Teflon lined column.



Outline

- Background
- Problem Statement
- Evaluation of the supply
- Summary



Summary

- Difficult to detect any excursion in incoming particles if the particles are smaller than the detection limit. Current state of the art detection limit is 45nm by liquid particle counter.
- Inline defect detection can also miss the defects on the wafer in similar situations where defects are smaller than the detection limit.
- Any particle excursion in any chemical can potentially degrade the inline defects.
- Sulfuric acid is usually produced using either glass or Teflon-lined steel absorption tower in high volume manufacturing environment.
- The difference in manufacturing process introduces variation in the type of defects both in quality and quantity.



Acknowledgment:

- *All colleagues in GLOBALFOUNDRIES*



Thank You



© 2013 GLOBALFOUNDRIES Inc. All rights reserved.



GLOBALFOUNDRIES®